80V N-CHANNEL ENHANCEMENT MODE MOSFET
PowerDI®5060-8

Product Summary

BV_{DSS}	$R_{DS(ON)}$	I_D T_C = 25°C
80V	7.8mΩ @ V_{GS} = 10V	83A
	11mΩ @ V_{GS} = 4.5V	70A

Features

- 100% Unclamped Inductive Switching (UIS) Test in Production – Ensures More Reliable and Robust End Application
- High Conversion Efficiency
- Low $R_{DS(ON)}$ – Minimizes On-State Losses
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/**

Description and Applications

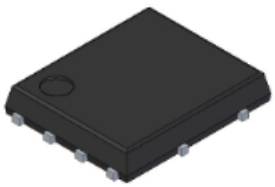
This new generation MOSFET is designed to minimize $R_{DS(ON)}$ yet maintain superior switching performance. This device is ideal for use in power management and load switches.

- DC-DC converters
- Load switches

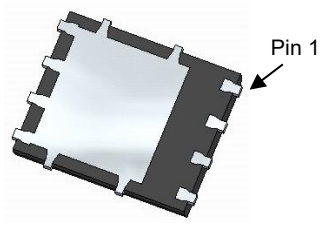
Mechanical Data

- Package: PowerDI5060-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram Below
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.097 grams (Approximate)

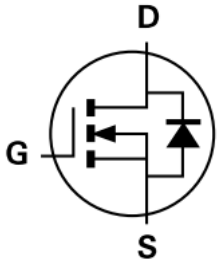
PowerDI5060-8



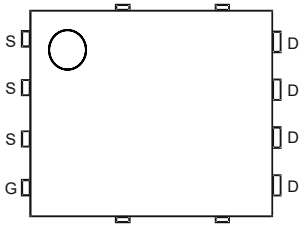
Top View



Bottom View



Internal Schematic



Top View
Pin Configuration

Ordering Information (Note 4)

Orderable Part Number	Package	Packing	
		Qty.	Carrier
DMT8008LPS-13	PowerDI5060-8	2,500	Tape & Reel

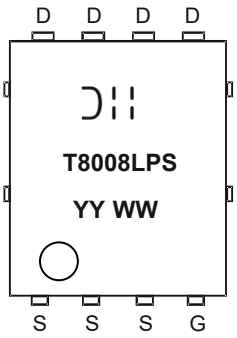
Notes:
1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

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Marking Information

PowerDI5060-8



= Manufacturer's Marking
T8008LPS = Product Type Marking Code
YYWW = Date Code Marking
YY = Year (ex: 26 = 2026)
WW = Week (01 to 53)

Maximum Ratings (@T_C = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	80	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current, V_{GS} = 10V (Note 5)	Steady State	T_C = 25°C T_C = 70°C	I_D	83 66	A
Maximum Continuous Body Diode Forward Current (Note 5)			I_S	69	A
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I_{DM}	330	A
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)			I_{SM}	330	A
Avalanche Current, L = 0.1mH (Note 6)			I_{AS}	23	A
Avalanche Energy, L = 0.1mH (Note 6)			E_{AS}	26.5	mJ

Thermal Characteristics (@T_C = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 7)	T_A = 25°C	P_D	1.3	W
Thermal Resistance, Junction to Ambient (Note 7)	Steady State	$R_{\theta JA}$	99	°C/W
Total Power Dissipation (Note 8)	T_A = 25°C	P_D	2.8	W
Thermal Resistance, Junction to Ambient (Note 8)	Steady State	$R_{\theta JA}$	45	°C/W
Total Power Dissipation (Note 5)	T_C = 25°C	P_D	83	W
Thermal Resistance, Junction to Case (Note 5)		$R_{\theta JC}$	1.5	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Notes:
5. Thermal resistance from junction to soldering point (on the exposed drain pad).
6. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
7. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
8. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

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Electrical Characteristics (@T_C = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV_{DSS}	80	—	—	V	V_{GS} = 0V, I_D = 1mA
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	μA	V_{DS} = 64V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS} = ±20V, V_{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.3	—	2.8	V	V_{DS} = V_{GS}, I_D = 1mA
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	5	7.8	mΩ	V_{GS} = 10V, I_D = 14A
		—	8	11		V_{GS} = 4.5V, I_D = 12A
Diode Forward Voltage	V_{SD}	—	0.8	1.2	V	V_{GS} = 0V, I_S = 14A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C_{iss}	—	2345	—	pF	V_{DS} = 40V, V_{GS} = 0V f = 1MHz
Output Capacitance	C_{oss}	—	842	—		
Reverse Transfer Capacitance	C_{rss}	—	51.9	—		
Gate Resistance	R_g	—	1.7	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge (V_{GS} = 4.5V)	Q_g	—	21.7	—	nC	V_{DD} = 40V, I_D = 2A
Total Gate Charge (V_{GS} = 10V)	Q_g	—	41.2	—		
Gate-Source Charge	Q_{gs}	—	5.0	—		
Gate-Drain Charge	Q_{gd}	—	10.6	—		
Turn-On Delay Time	$t_{D(ON)}$	—	5.8	—	ns	V_{DD} = 40V, V_{GS} = 10V I_D = 2A, R_g = 1.6Ω
Turn-On Rise Time	t_R	—	5.4	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	24.5	—		
Turn-Off Fall Time	t_F	—	43.2	—		
Body Diode Reverse-Recovery Time	t_{RR}	—	61	—	ns	I_F = 2A, di/dt = 100A/μs
Body Diode Reverse-Recovery Charge	Q_{RR}	—	181	—	nC	

Notes: 9. Short duration pulse test used to minimize self-heating effect.
10. Guaranteed by design. Not subject to product testing.

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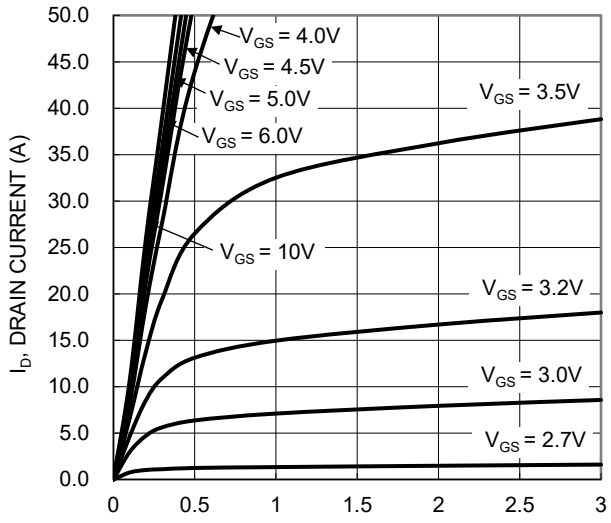


Figure 1. Typical Output Characteristic

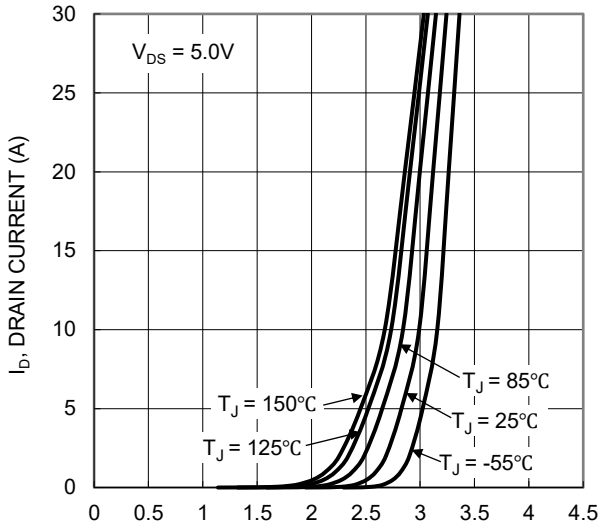


Figure 2. Typical Transfer Characteristic

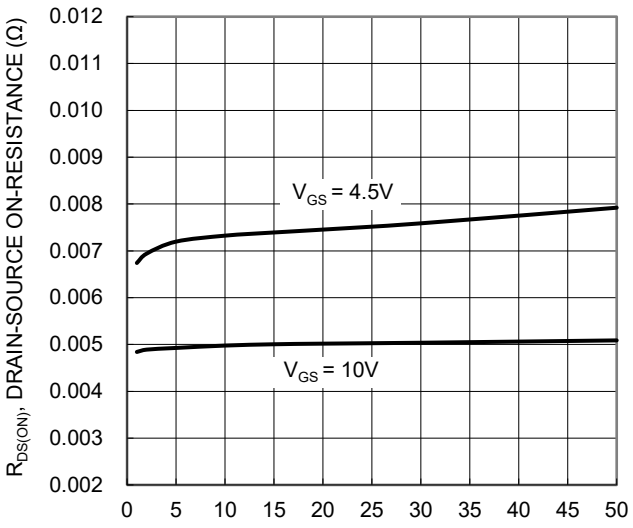


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

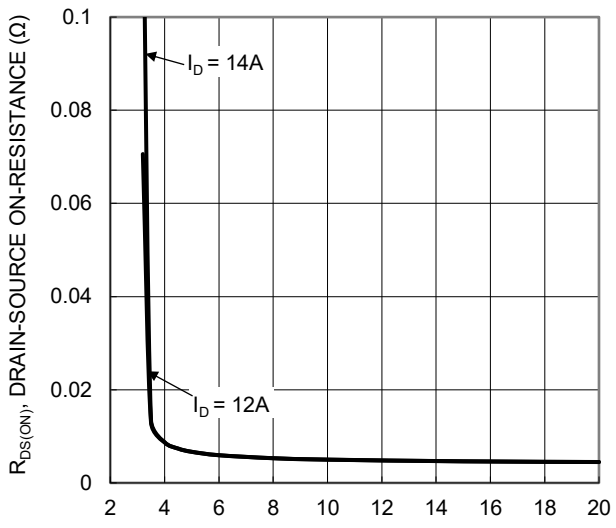


Figure 4. Typical Transfer Characteristic

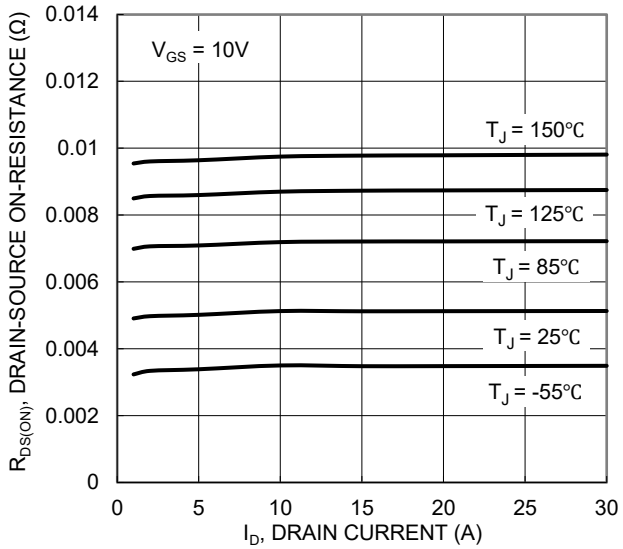


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

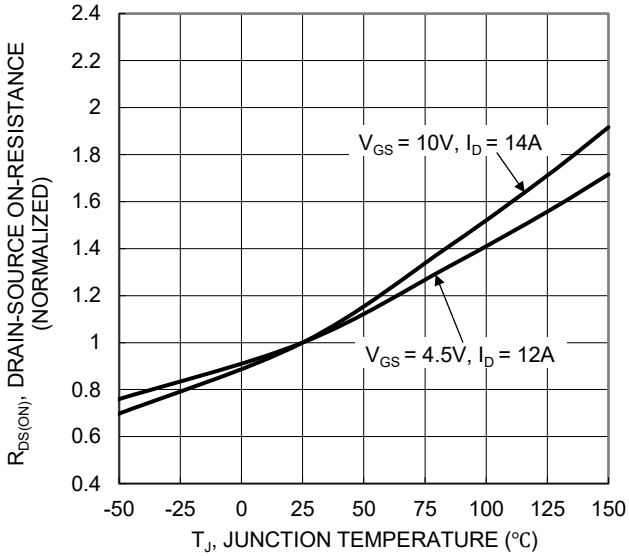


Figure 6. On-Resistance Variation with Temperature

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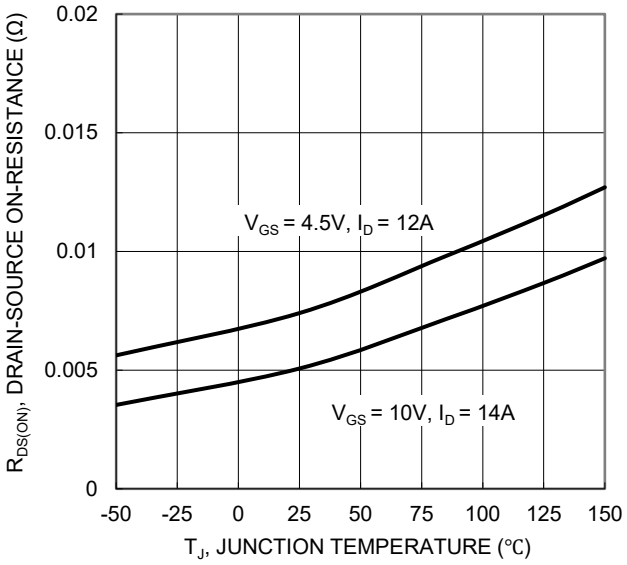


Figure 7. On-Resistance Variation with Temperature

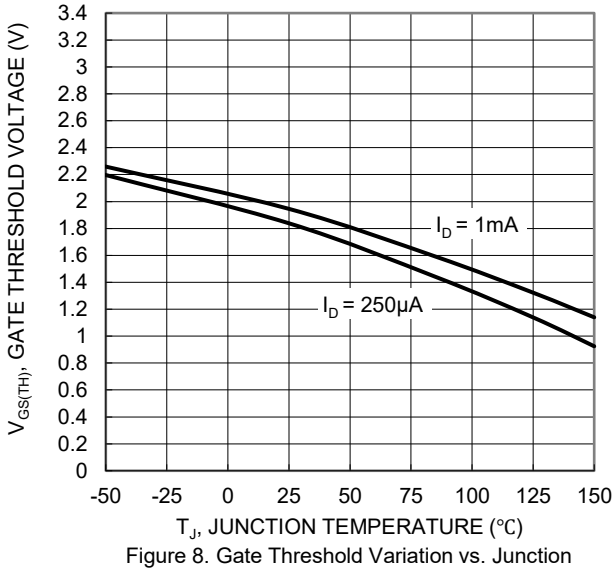


Figure 8. Gate Threshold Variation vs. Junction Temperature

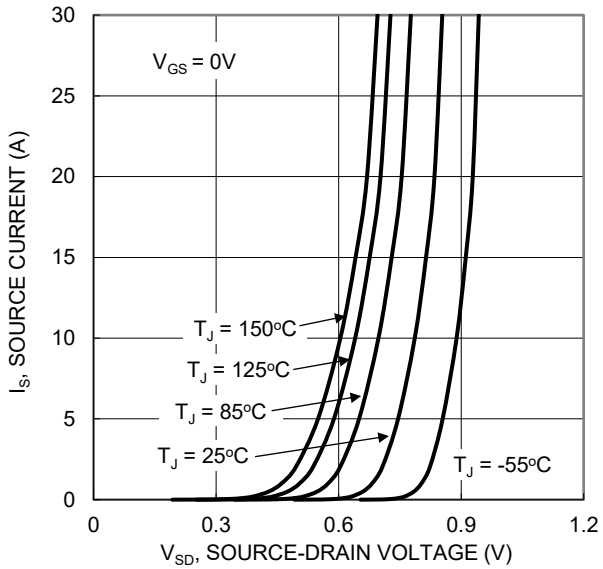


Figure 9. Diode Forward Voltage vs. Current

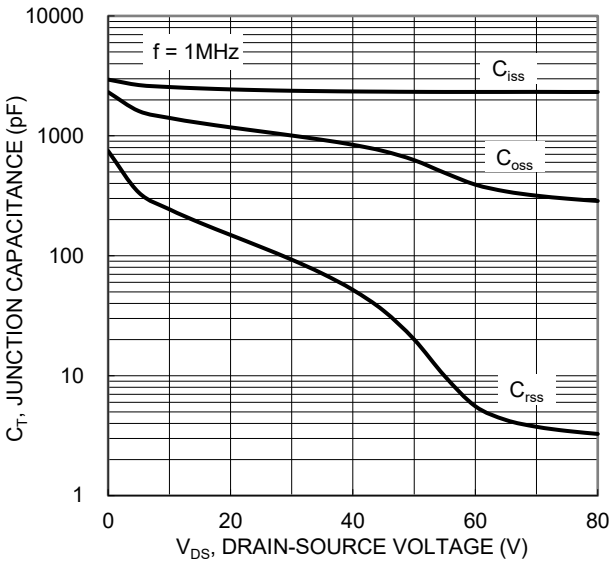


Figure 10. Typical Junction Capacitance

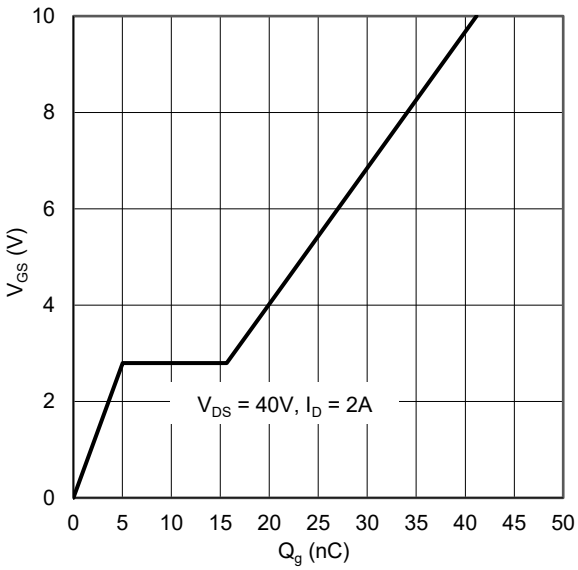


Figure 11. Gate Charge

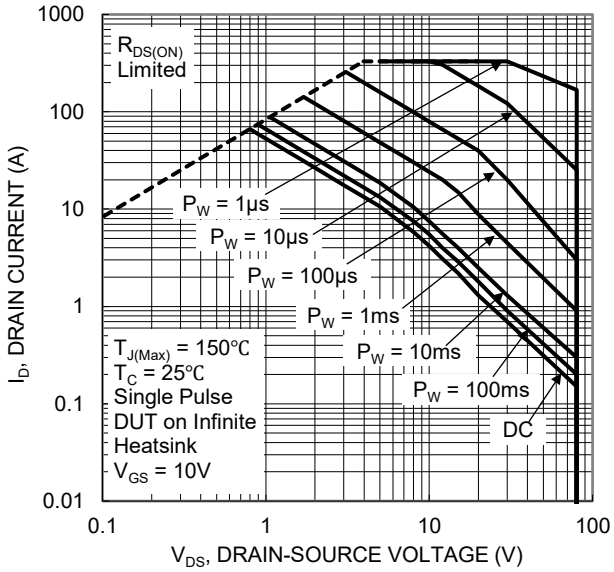


Figure 12. SOA, Safe Operation Area

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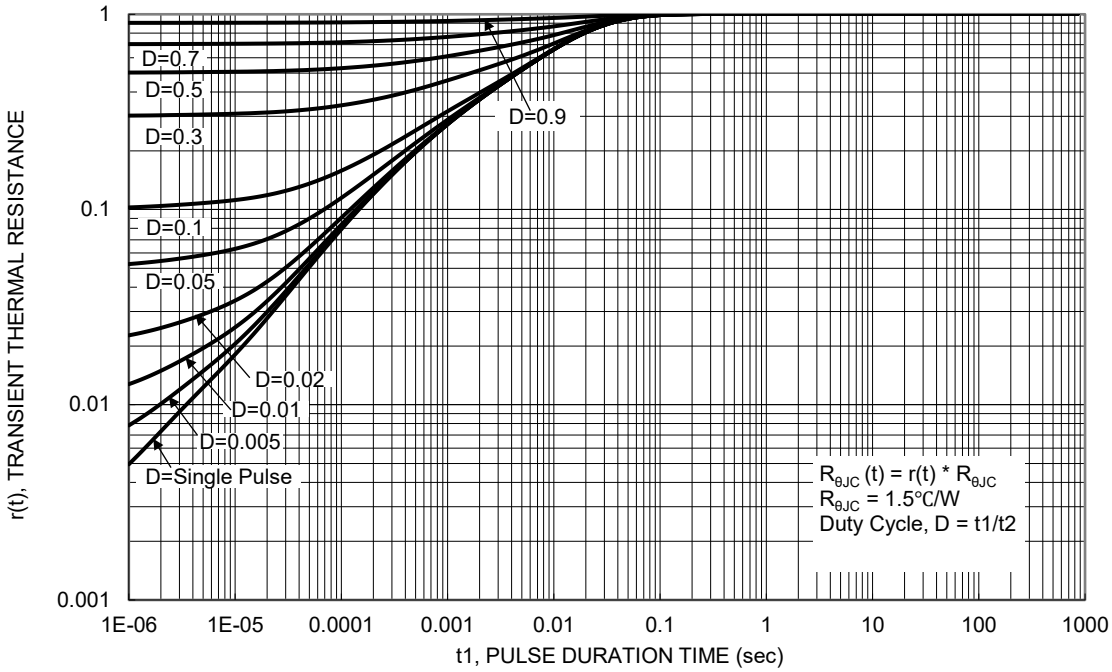


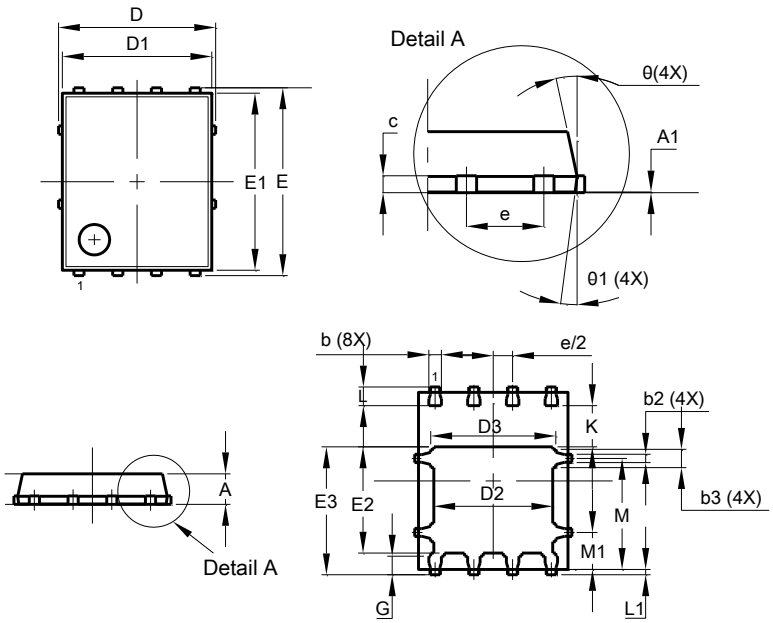
Figure 13. Transient Thermal Resistance

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Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

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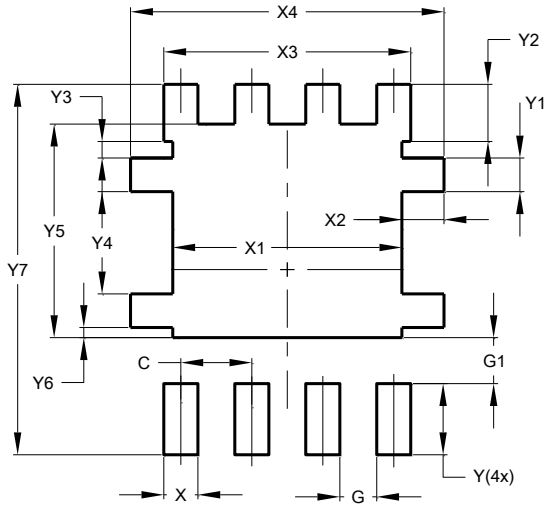


PowerDI5060-8			
Dim	**Min**	**Max**	**Typ**
A	0.90	1.10	1.00
A1	0.00	0.05	–
b	0.33	0.51	0.41
b2	0.200	0.350	0.273
b3	0.40	0.80	0.60
c	0.230	0.330	0.277
D	5.15 BSC		
D1	4.70	5.10	4.90
D2	3.70	4.10	3.90
D3	3.90	4.30	4.10
E	6.15 BSC		
E1	5.60	6.00	5.80
E2	3.28	3.68	3.48
E3	3.99	4.39	4.19
e	1.27 BSC		
G	0.51	0.71	0.61
K	0.51	–	–
L	0.51	0.71	0.61
L1	0.100	0.200	0.175
M	3.235	4.035	3.635
M1	1.00	1.40	1.21
Θ	10°	12°	11°
Θ1	6°	8°	7°
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI5060-8



Dimensions	Value (in mm)
C	1.270
G	0.660
G1	0.820
X	0.610
X1	4.100
X2	0.755
X3	4.420
X4	5.610
Y	1.270
Y1	0.600
Y2	1.020
Y3	0.295
Y4	1.825
Y5	3.810
Y6	0.180
Y7	6.610

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